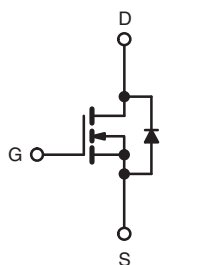
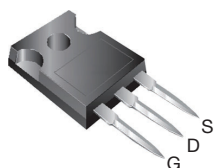


## Power MOSFET

### PRODUCT SUMMARY

|                           |                        |       |
|---------------------------|------------------------|-------|
| $V_{DS}$ (V)              | 200                    |       |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ | 0.055 |
| $Q_g$ (Max.) (nC)         | 230                    |       |
| $Q_{gs}$ (nC)             | 42                     |       |
| $Q_{gd}$ (nC)             | 110                    |       |
| Configuration             | Single                 |       |

**TO-247AC**


N-Channel MOSFET

### FEATURES

- Dynamic  $dV/dt$  Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC


**RoHS\***  
COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

### ORDERING INFORMATION

|                |                           |
|----------------|---------------------------|
| Package        | TO-247AC                  |
| Lead (Pb)-free | IRFP260PbF<br>SiHFP260-E3 |
| SnPb           | IRFP260<br>SiHFP260       |

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

| PARAMETER                                        | SYMBOL                           | LIMIT                             | UNIT                |
|--------------------------------------------------|----------------------------------|-----------------------------------|---------------------|
| Drain-Source Voltage                             | $V_{DS}$                         | 200                               | V                   |
| Gate-Source Voltage                              | $V_{GS}$                         | $\pm 20$                          |                     |
| Continuous Drain Current                         | $V_{GS} \text{ at } 10\text{ V}$ | $T_C = 25\text{ }^\circ\text{C}$  | A                   |
|                                                  |                                  | $T_C = 100\text{ }^\circ\text{C}$ |                     |
| Pulsed Drain Current <sup>a</sup>                | $I_{DM}$                         | 180                               |                     |
| Linear Derating Factor                           |                                  | 2.2                               | W/ $^\circ\text{C}$ |
| Single Pulse Avalanche Energy <sup>b</sup>       | $E_{AS}$                         | 1000                              | mJ                  |
| Repetitive Avalanche Current <sup>a</sup>        | $I_{AR}$                         | 46                                | A                   |
| Repetitive Avalanche Energy <sup>a</sup>         | $E_{AR}$                         | 28                                | mJ                  |
| Maximum Power Dissipation                        | $T_C = 25\text{ }^\circ\text{C}$ | $P_D$                             | 280                 |
| Peak Diode Recovery $dV/dt$ <sup>c</sup>         | $dV/dt$                          | 5.0                               | V/ns                |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$                   | - 55 to + 150                     | $^\circ\text{C}$    |
| Soldering Recommendations (Peak Temperature)     | for 10 s                         | 300 <sup>d</sup>                  |                     |
| Mounting Torque                                  | 6-32 or M3 screw                 | 10                                |                     |
|                                                  |                                  | 1.1                               |                     |

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 708\text{ }\mu\text{H}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 46\text{ A}$  (see fig. 12).
- $I_{SD} \leq 46\text{ A}$ ,  $dI/dt \leq 230\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

| PARAMETER                           | SYMBOL     | TYP. | MAX. | UNIT |
|-------------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient         | $R_{thJA}$ | -    | 40   | °C/W |
| Case-to-Sink, Flat, Greased Surface | $R_{thCS}$ | 0.24 | -    |      |
| Maximum Junction-to-Case (Drain)    | $R_{thJC}$ | -    | 0.45 |      |

**SPECIFICATIONS** ( $T_J = 25\text{ °C}$ , unless otherwise noted)

| PARAMETER                                 | SYMBOL                           | TEST CONDITIONS                                                                                                             |                                                                                   | MIN. | TYP. | MAX.  | UNIT |
|-------------------------------------------|----------------------------------|-----------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------|------|------|-------|------|
| Static                                    |                                  |                                                                                                                             |                                                                                   |      |      |       |      |
| Drain-Source Breakdown Voltage            | V <sub>DS</sub>                  | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                              |                                                                                   | 200  | -    | -     | V    |
| V <sub>DS</sub> Temperature Coefficient   | ΔV <sub>DS</sub> /T <sub>J</sub> | Reference to 25 °C, I <sub>D</sub> = 1 mA                                                                                   |                                                                                   | -    | 0.24 | -     | V/°C |
| Gate-Source Threshold Voltage             | V <sub>GS(th)</sub>              | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                 |                                                                                   | 2.0  | -    | 4.0   | V    |
| Gate-Source Leakage                       | I <sub>GSS</sub>                 | V <sub>GS</sub> = ± 20 V                                                                                                    |                                                                                   | -    | -    | ± 100 | nA   |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>                 | V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V                                                                              |                                                                                   | -    | -    | 25    | μA   |
|                                           |                                  | V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                                                     |                                                                                   | -    | -    | 250   |      |
| Drain-Source On-State Resistance          | R <sub>DS(on)</sub>              | V <sub>GS</sub> = 10 V                                                                                                      | I <sub>D</sub> = 28 A <sup>b</sup>                                                | -    | -    | 0.055 | Ω    |
| Forward Transconductance                  | g <sub>fs</sub>                  | V <sub>DS</sub> = 50 V, I <sub>D</sub> = 28 A <sup>b</sup>                                                                  |                                                                                   | 24   | -    | -     | S    |
| Dynamic                                   |                                  |                                                                                                                             |                                                                                   |      |      |       |      |
| Input Capacitance                         | C <sub>iss</sub>                 | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 25 V,<br>f = 1.0 MHz, see fig. 5                                                |                                                                                   | -    | 5200 | -     | pF   |
| Output Capacitance                        | C <sub>oss</sub>                 |                                                                                                                             |                                                                                   | -    | 1200 | -     |      |
| Reverse Transfer Capacitance              | C <sub>rss</sub>                 |                                                                                                                             |                                                                                   | -    | 310  | -     |      |
| Total Gate Charge                         | Q <sub>g</sub>                   | V <sub>GS</sub> = 10 V                                                                                                      | I <sub>D</sub> = 46 A, V <sub>DS</sub> = 160 V,<br>see fig. 6 and 13 <sup>b</sup> | -    | -    | 230   | nC   |
| Gate-Source Charge                        | Q <sub>gs</sub>                  |                                                                                                                             |                                                                                   | -    | -    | 42    |      |
| Gate-Drain Charge                         | Q <sub>gd</sub>                  |                                                                                                                             |                                                                                   | -    | -    | 110   |      |
| Turn-On Delay Time                        | t <sub>d(on)</sub>               | V <sub>DD</sub> = 100 V, I <sub>D</sub> = 46 A,<br>R <sub>g</sub> = 4.3 Ω, R <sub>D</sub> = 2.1 Ω, see fig. 10 <sup>b</sup> |                                                                                   | -    | 23   | -     | ns   |
| Rise Time                                 | t <sub>r</sub>                   |                                                                                                                             |                                                                                   | -    | 120  | -     |      |
| Turn-Off Delay Time                       | t <sub>d(off)</sub>              |                                                                                                                             |                                                                                   | -    | 100  | -     |      |
| Fall Time                                 | t <sub>f</sub>                   |                                                                                                                             |                                                                                   | -    | 94   | -     |      |
| Internal Drain Inductance                 | L <sub>D</sub>                   | Between lead,<br>6 mm (0.25") from<br>package and center of<br>die contact                                                  |                                                                                   | -    | 5.0  | -     | nH   |
| Internal Source Inductance                | L <sub>S</sub>                   |                                                                                                                             |                                                                                   | -    | 13   | -     |      |
| Drain-Source Body Diode Characteristics   |                                  |                                                                                                                             |                                                                                   |      |      |       |      |
| Continuous Source-Drain Diode Current     | I <sub>S</sub>                   | MOSFET symbol<br>showing the<br>integral reverse<br>p - n junction diode                                                    |                                                                                   | -    | -    | 46    | A    |
| Pulsed Diode Forward Current <sup>a</sup> | I <sub>SM</sub>                  |                                                                                                                             |                                                                                   | -    | -    | 180   |      |
| Body Diode Voltage                        | V <sub>SD</sub>                  | T <sub>J</sub> = 25 °C, I <sub>S</sub> = 46 A, V <sub>GS</sub> = 0 V <sup>b</sup>                                           |                                                                                   | -    | -    | 1.8   | V    |
| Body Diode Reverse Recovery Time          | t <sub>rr</sub>                  | T <sub>J</sub> = 25 °C, I <sub>F</sub> = 46 A, dI/dt = 100 A/μs <sup>b</sup>                                                |                                                                                   | -    | 390  | 590   | ns   |
| Body Diode Reverse Recovery Charge        | Q <sub>rr</sub>                  |                                                                                                                             |                                                                                   | -    | 4.8  | 7.2   | μC   |
| Forward Turn-On Time                      | t <sub>on</sub>                  | Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )                           |                                                                                   |      |      |       |      |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

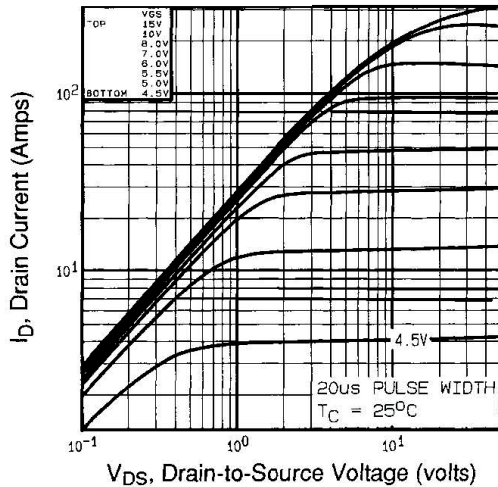


Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$

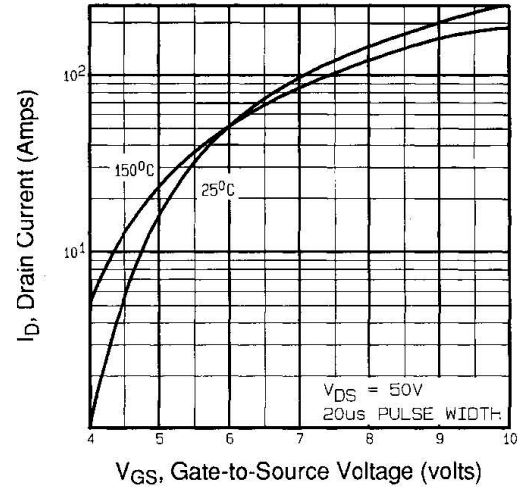


Fig. 3 - Typical Transfer Characteristics

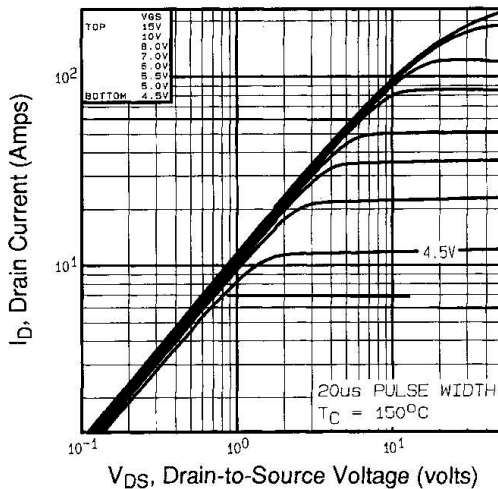


Fig. 2 - Typical Output Characteristics,  $T_C = 150^\circ\text{C}$

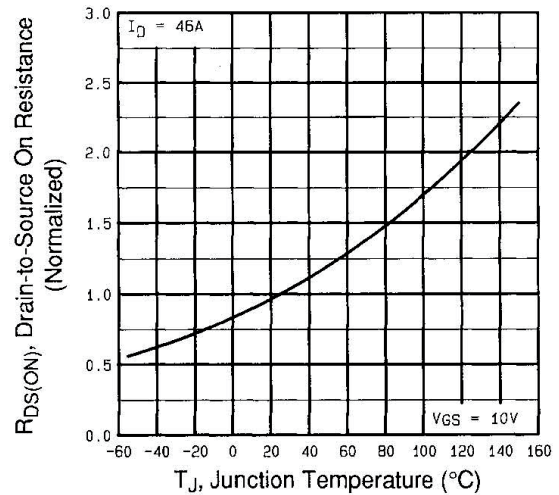


Fig. 4 - Normalized On-Resistance vs. Temperature

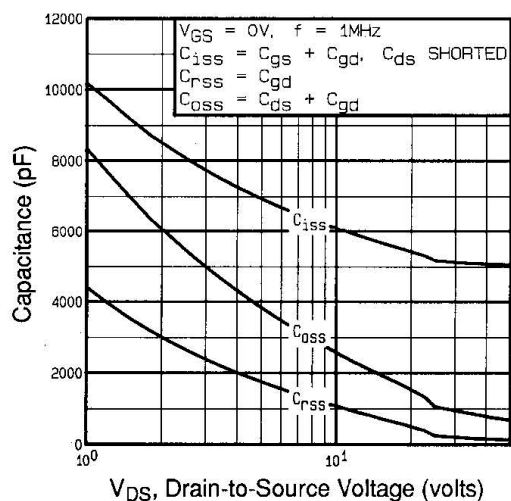


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

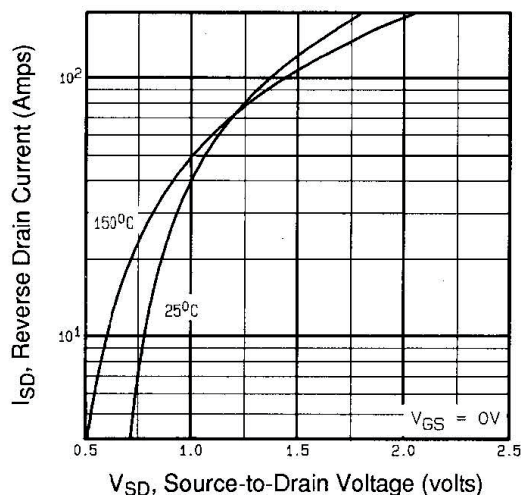


Fig. 7 - Typical Source-Drain Diode Forward Voltage

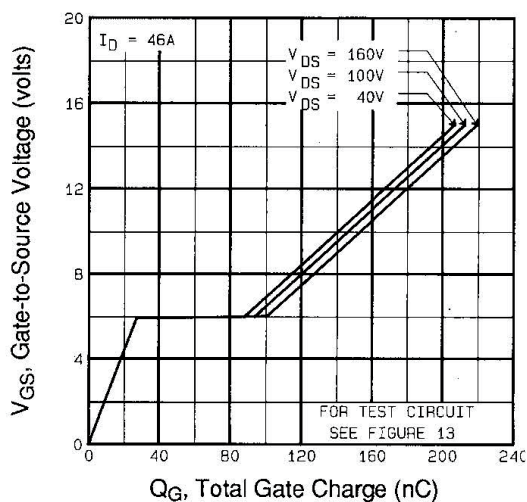


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

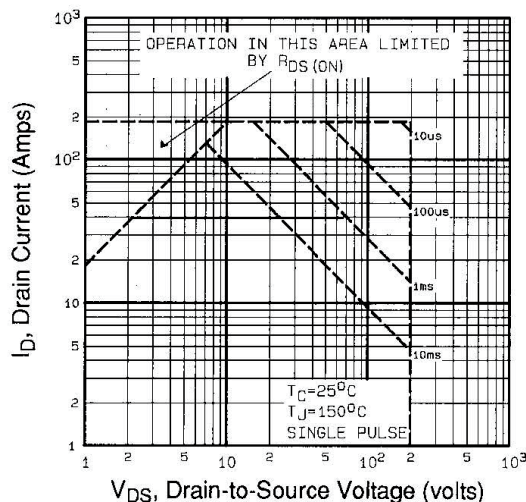


Fig. 8 - Maximum Safe Operating Area

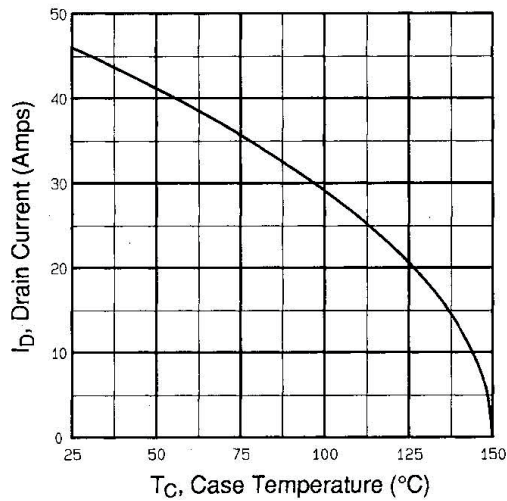


Fig. 9 - Maximum Drain Current vs. Case Temperature

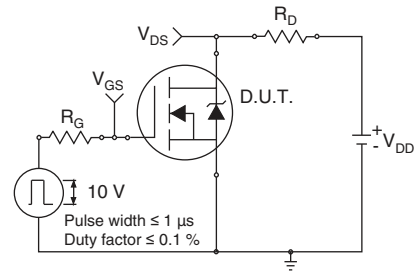


Fig. 10a - Switching Time Test Circuit

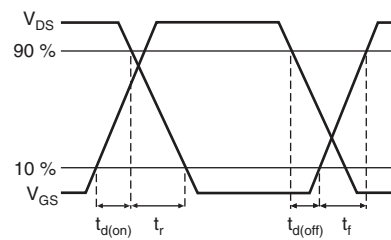


Fig. 10b - Switching Time Waveforms

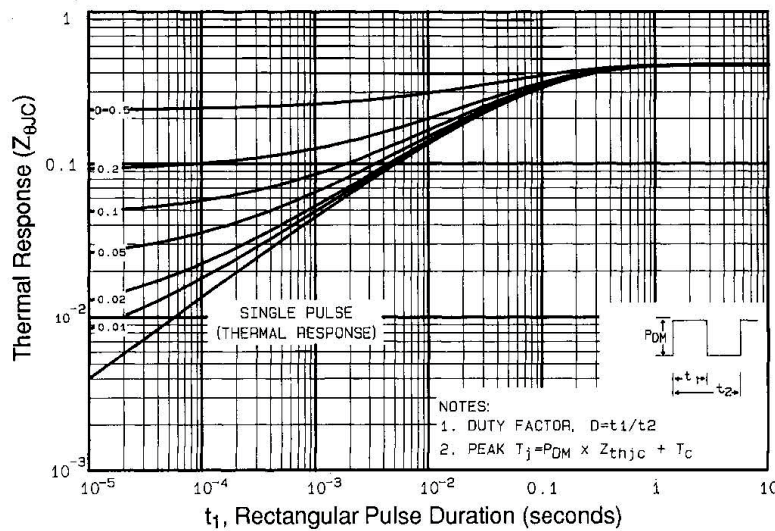


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

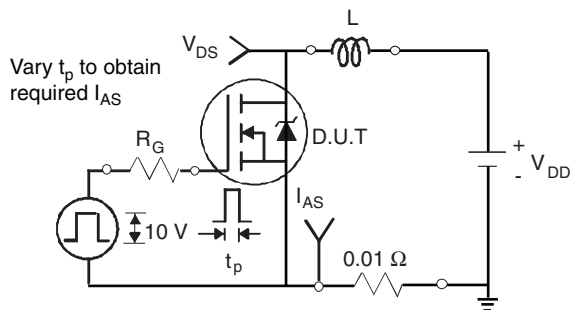


Fig. 12a - Unclamped Inductive Test Circuit

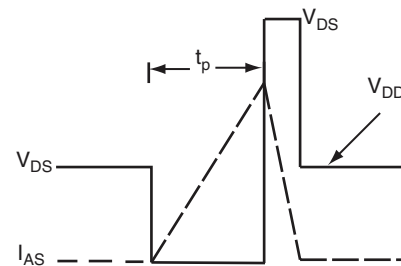


Fig. 12b - Unclamped Inductive Waveforms

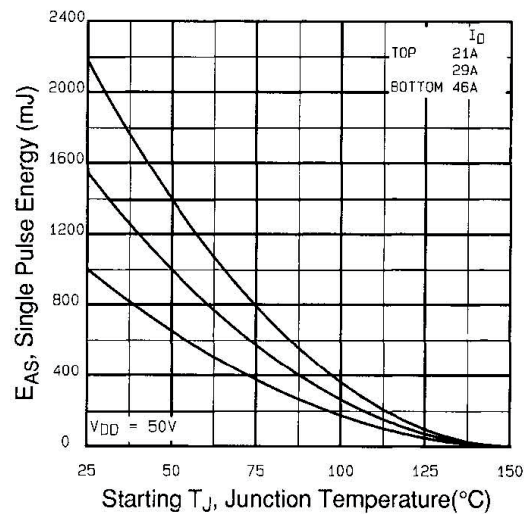


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

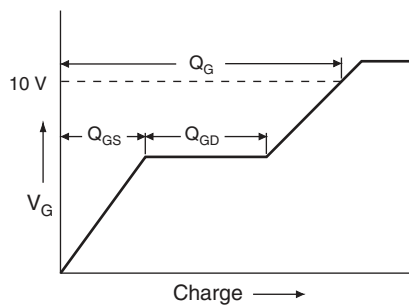


Fig. 13a - Basic Gate Charge Waveform

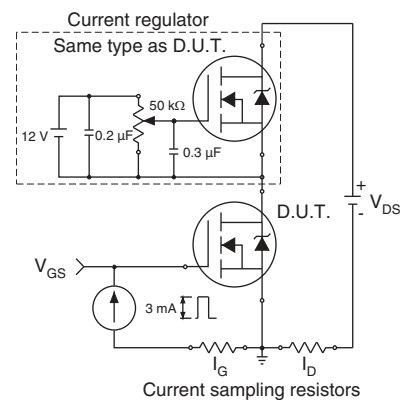
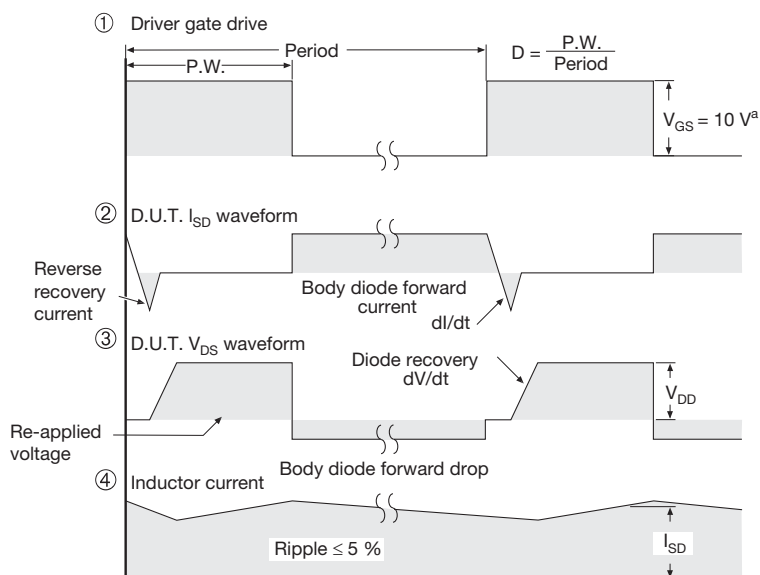


Fig. 13b - Gate Charge Test Circuit

The diagram shows a switching power supply circuit with the following components and layout considerations:

- Input:** A square wave voltage source (1) is connected in series with a resistor  $R_g$  to the gate of the first MOSFET.
- First MOSFET:** A MOSFET (2) with its drain connected to the primary of a transformer. Its source is connected to ground.
- Transformer:** A transformer with its secondary connected to the gate of the second MOSFET.
- Second MOSFET:** A MOSFET (3) with its drain connected to the positive output terminal (+) and its source connected to ground.
- Output:** The output is taken from the drain of the second MOSFET, passing through an inductor (4) and a resistor to the positive output terminal (+). The negative output terminal (-) is connected to ground.
- Ground Plane:** A common ground plane is shown at the bottom, connected to the sources of both MOSFETs and the negative output terminal.
- Layout Considerations:**
  - Low stray inductance
  - Ground plane
  - Low leakage inductance current transformer



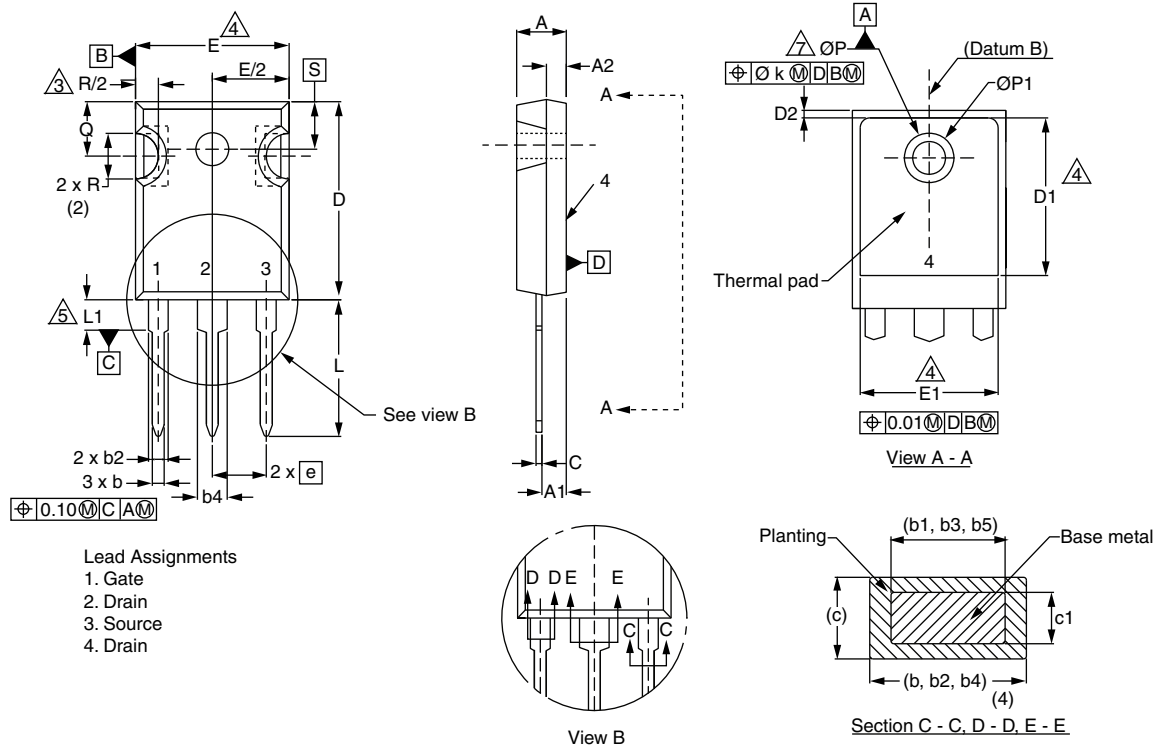
a.  $V_{GS} = 5 \text{ V}$  for logic level devices

**Fig. 14 - For N-Channel**

THE PRODUCT DESCRIBED HEREIN AND THIS DATASHEET ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT [www.vishay.com/doc?91000](http://www.vishay.com/doc?91000)



## TO-247AC (High Voltage)



| DIM. | MILLIMETERS |       | INCHES |       |
|------|-------------|-------|--------|-------|
|      | MIN.        | MAX.  | MIN.   | MAX.  |
| A    | 4.58        | 5.31  | 0.180  | 0.209 |
| A1   | 2.21        | 2.59  | 0.087  | 0.102 |
| A2   | 1.17        | 2.49  | 0.046  | 0.098 |
| b    | 0.99        | 1.40  | 0.039  | 0.055 |
| b1   | 0.99        | 1.35  | 0.039  | 0.053 |
| b2   | 1.53        | 2.39  | 0.060  | 0.094 |
| b3   | 1.65        | 2.37  | 0.065  | 0.093 |
| b4   | 2.42        | 3.43  | 0.095  | 0.135 |
| b5   | 2.59        | 3.38  | 0.102  | 0.133 |
| c    | 0.38        | 0.86  | 0.015  | 0.034 |
| c1   | 0.38        | 0.76  | 0.015  | 0.030 |
| D    | 19.71       | 20.82 | 0.776  | 0.820 |
| D1   | 13.08       | -     | 0.515  | -     |

| DIM. | MILLIMETERS |       | INCHES    |       |
|------|-------------|-------|-----------|-------|
|      | MIN.        | MAX.  | MIN.      | MAX.  |
| D2   | 0.51        | 1.30  | 0.020     | 0.051 |
| E    | 15.29       | 15.87 | 0.602     | 0.625 |
| E1   | 13.72       | -     | 0.540     | -     |
| e    | 5.46 BSC    |       | 0.215 BSC |       |
| Ø k  | 0.254       |       | 0.010     |       |
| L    | 14.20       | 16.25 | 0.559     | 0.640 |
| L1   | 3.71        | 4.29  | 0.146     | 0.169 |
| N    | 7.62 BSC    |       | 0.300 BSC |       |
| Ø P  | 3.51        | 3.66  | 0.138     | 0.144 |
| Ø P1 | -           | 7.39  | -         | 0.291 |
| Q    | 5.31        | 5.69  | 0.209     | 0.224 |
| R    | 4.52        | 5.49  | 0.178     | 0.216 |
| S    | 5.51 BSC    |       | 0.217 BSC |       |

ECN: X13-0103-Rev. D, 01-Jul-13  
DWG: 5971

### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Contour of slot optional.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions D1 and E1.
5. Lead finish uncontrolled in L1.
6. Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154").
7. Outline conforms to JEDEC outline TO-247 with exception of dimension c.
8. Xian and Mingxin actually photo.

